

MC74VHC1G132

2-Input NAND Schmitt-Trigger

The MC74VHC1G132 is a single gate CMOS Schmitt NAND trigger fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output.

The MC74VHC1G132 input structure provides protection when voltages up to 7.0 V are applied, regardless of the supply voltage. This allows the MC74VHC1G132 to be used to interface 5.0 V circuits to 3.0 V circuits.

The MC74VHC1G132 can be used to enhance noise immunity or to square up slowly changing waveforms.

Features

- High Speed: $t_{PD} = 3.6 \text{ ns}$ (Typ) at $V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation: $I_{CC} = 1.0 \mu\text{A}$ (Max) at $T_A = 25^\circ\text{C}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- Chip Complexity: FETs = 68; Equivalent Gates = 16
- Pb-Free Packages are Available

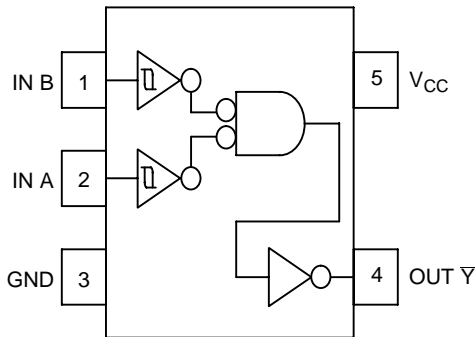


Figure 1. Pinout (Top View)

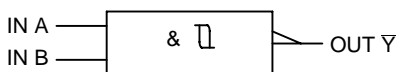


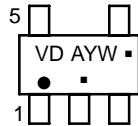
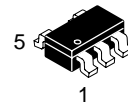
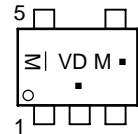
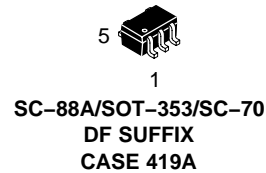
Figure 2. Logic Symbol



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MARKING DIAGRAMS



- VD = Device Code
- M = Date Code*
- A = Assembly Location
- Y = Year
- W = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

PIN ASSIGNMENT	
1	IN B
2	IN A
3	GND
4	OUT \bar{Y}
5	V_{CC}

FUNCTION TABLE		
Inputs		Output
A	B	\bar{Y}
L	L	H
L	H	H
H	L	H
H	H	L

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MC74VHC1G132

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0	V
V _{IN}	DC Input Voltage	-0.5 to +7.0	V
V _{OUT}	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	-20	mA
I _{OK}	DC Output Diode Current	±20	mA
I _{OUT}	DC Output Sink Current	±12.5	mA
I _{CC}	DC Supply Current per Supply Pin	±25	mA
T _{STG}	Storage Temperature Range	-65 to +150	°C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C
T _J	Junction Temperature Under Bias	+150	°C
θ _{JA}	Thermal Resistance	SC70-5/SC-88A (Note 1) TSOP-5 350 230	°C/W
P _D	Power Dissipation in Still Air at 85°C	SC70-5/SC-88A TSOP-5 150 200	mW
MSL	Moisture Sensitivity	Level 1	
F _R	Flammability Rating	Oxygen Index: 28 to 34 UL 94 V-0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4) >2000 >200 N/A	V
I _{LATCHUP}	Latchup Performance	Above V _{CC} and Below GND at 125°C (Note 5)	±500 mA

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.
2. Tested to EIA/JESD22-A114-A.
3. Tested to EIA/JESD22-A115-A.
4. Tested to JESD22-C101-A.
5. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	2.0	5.5	V
V _{IN}	DC Input Voltage	0.0	5.5	V
V _{OUT}	DC Output Voltage	0.0	V _{CC}	V
T _A	Operating Temperature Range	-55	+125	°C
t _r , t _f	Input Rise and Fall Time	V _{CC} = 3.3 V ± 0.3 V V _{CC} = 5.0 V ± 0.5 V	- No Limit No Limit	ns/V

Device Junction Temperature versus Time to 0.1% Bond Failures

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

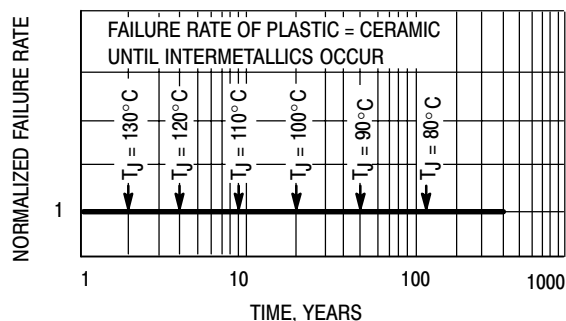


Figure 3. Failure Rate vs. Time Junction Temperature

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DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V _{CC} (V)	T _A = 25°C			T _A ≤ 85°C		-55 ≤ T _A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V _{T+}	Positive Threshold Voltage		3.0	1.50	1.88	2.25	1.50	2.25	1.50	2.25	V
			4.5	2.35	2.66	3.10	2.35	3.10	2.35	3.10	
			5.5	2.80	3.21	3.70	2.80	3.70	2.80	3.70	
V _{T-}	Negative Threshold Voltage		3.0	0.65	1.03	1.40	0.65	1.40	0.65	1.40	V
			4.5	1.10	1.62	2.10	1.10	2.10	1.10	2.10	
			5.5	1.45	2.02	2.60	1.45	2.60	1.45	2.60	
V _H	Hysteresis Voltage		3.0	0.30	0.85	1.60	0.30	1.60	0.30	1.60	V
			4.5	0.40	1.05	2.00	0.40	2.00	0.40	2.00	
			5.5	0.50	1.20	2.25	0.50	2.25	0.50	2.25	
V _{OH}	Minimum High-Level Output Voltage I _{OH} = -50 μA	V _{IN} = V _{CC} or GND	2.0	1.9	2.0		1.9		1.9		V
		V _{IN} = V _{IH} or V _{IL} I _{OH} = -50 μA	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.5		
		I _{OH} = -4 mA I _{OH} = -8 mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		
V _{OL}	Maximum Low-Level Output Voltage	V _{IN} = V _{IH} or V _{IL} I _{OL} = 50 μA	2.0		0.0	0.1		0.1		0.1	V
			3.0		0.0	0.1		0.1		0.1	
			4.5		0.0	0.1		0.1		0.1	
			3.0			0.36		0.44		0.52	V
			4.5			0.36		0.44		0.52	
I _{IN}	Maximum Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μA
I _{CC}	Maximum Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5			1.0		20		40	μA

AC ELECTRICAL CHARACTERISTICS C_{load} = 50 pF, Input t_r/t_f = 3.0 ns

Symbol	Parameter	Test Conditions	T _A = 25°C			T _A ≤ 85°C		-55 ≤ T _A ≤ 125°C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, A or B to \bar{Y}	V _{CC} = 3.3 ± 0.3 V C _L = 15 pF C _L = 50 pF		4.6	11.9	1.0	14.0	1.0	16.1	ns
		V _{CC} = 5.0 ± 0.5 V C _L = 15 pF C _L = 50 pF		3.6	7.7	1.0	9.0	1.0	10.3	
				4.3	9.7	1.0	11.0	1.0	12.3	
C _{IN}	Maximum Input Capacitance			5.5	10		10		10	pF

C _{PD}	Power Dissipation Capacitance (Note 6)	Typical @ 25°C, V _{CC} = 5.0 V		pF
		11		

6. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

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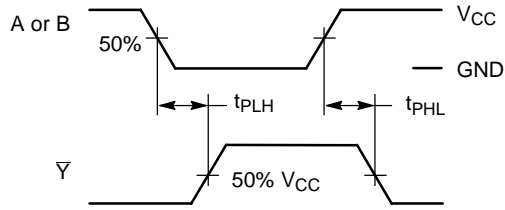
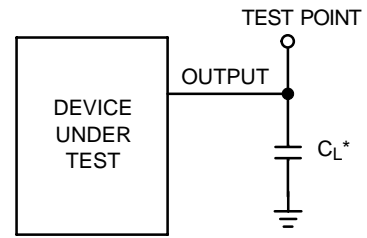


Figure 4. Switching Waveforms



*Includes all probe and jig capacitance

Figure 5. Test Circuit

DEVICE ORDERING INFORMATION

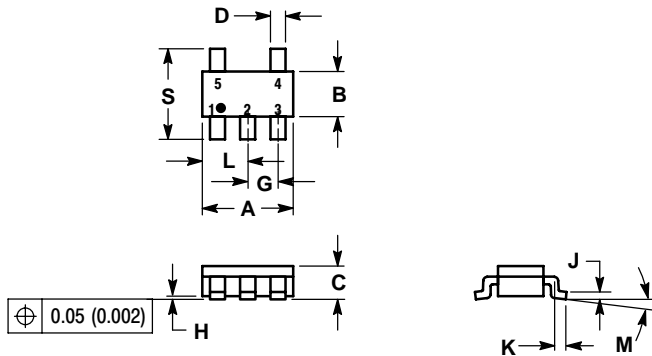
Device Order Number	Package Type	Tape and Reel Size [†]
MC74VHC1G132DFT1	SC70-5/SC-88A/SOT-353	178 mm (7 in) 3000 Units / Tape & Reel
M74VHC1G132DFT1G	SC70-5/SC-88A/SOT-353 (Pb-Free)	178 mm (7 in) 3000 Units / Tape & Reel
MC74VHC1G132DFT2	SC70-5/SC-88A/SOT-353	178 mm (7 in) 3000 Units / Tape & Reel
M74VHC1G132DFT2G	SC70-5/SC-88A/SOT-353 (Pb-Free)	178 mm (7 in) 3000 Units / Tape & Reel
MC74VHC1G132DTT1	SOT23-5/TSOP-5SC59-5	178 mm (7 in) 3000 Units / Tape & Reel
M74VHC1G132DTT1G	SOT23-5/TSOP-5SC59-5 (Pb-Free)	178 mm (7 in) 3000 Units / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MC74VHC1G132

PACKAGE DIMENSIONS

TSOP-5 / SOT23-5 / SC59-5
DT SUFFIX
CASE 483-02
ISSUE D

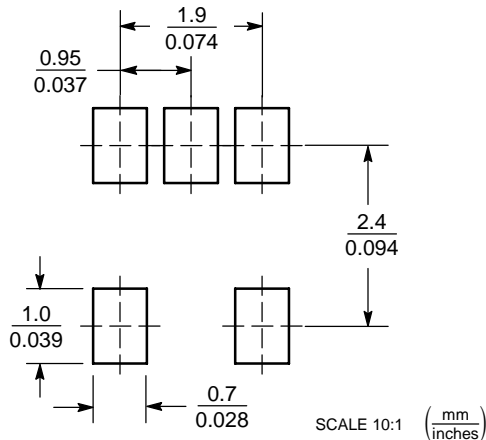


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. A AND B DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.90	3.10	0.1142	0.1220
B	1.30	1.70	0.0512	0.0669
C	0.90	1.10	0.0354	0.0433
D	0.25	0.50	0.0098	0.0197
G	0.85	1.05	0.0335	0.0413
H	0.013	0.100	0.0005	0.0040
J	0.10	0.26	0.0040	0.0102
K	0.20	0.60	0.0079	0.0236
L	1.25	1.55	0.0493	0.0610
M	0°	10°	0°	10°
S	2.50	3.00	0.0985	0.1181

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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